

Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (Typ.)
Channel-1	30	0.0095 at V _{GS} = 10 V	30 ^a	5.6 nC
		0.0137 at V _{GS} = 4.5 V	22	
Channel-2	30	0.0051 at V _{GS} = 10 V	40 ^a	10.1 nC
		0.0070 at V _{GS} = 4.5 V	40 ^a	

FEATURES

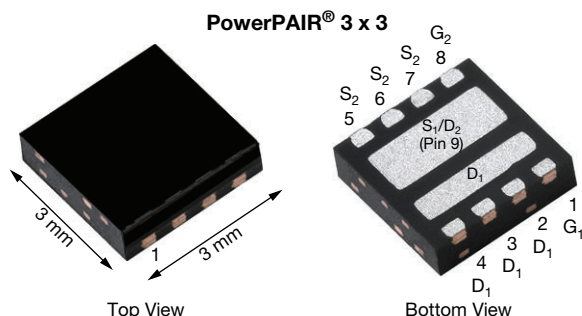
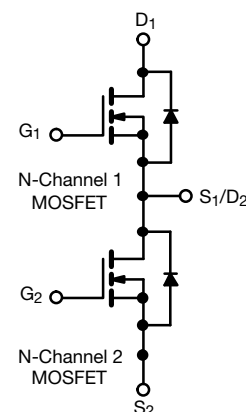
- PowerPAIR® Optimizes high-side and low-side MOSFETs for synchronous buck converters
- TrenchFET® power Mosfets
- 100 % R_g and UIS tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous buck
 - Battery charging
 - Computer system power
 - Graphic cards
- POL



Ordering Information:

SiZ340DT-T1-GE3 (lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	+20, -16		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	30 ^a	40 ^a	A
	T _C = 70 °C		26.5	40 ^a	
	T _A = 25 °C		15.6 ^{b,c}	22.6 ^{b,c}	
	T _A = 70 °C		12.4 ^{b,c}	18.1 ^{b,c}	
Pulsed Drain Current (t = 100 μs)		I _{DM}	100	150	
Continuous Source Drain Diode Current	T _C = 25 °C	I _S	13.9	26	
	T _A = 25 °C		3.1 ^{b,c}	3.5 ^{b,c}	
Avalanche Current	L = 0.1 mH	I _{AS}	10	15	
Single Pulse Avalanche Energy		E _{AS}	5	11	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	16.7	31	W
	T _C = 70 °C		10.7	20	
	T _A = 25 °C		3.7 ^{b,c}	4.2 ^{b,c}	
	T _A = 70 °C		2.4 ^{b,c}	2.7 ^{b,c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{d,e}			260		

Notes

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR 3 x 3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.

**THERMAL RESISTANCE RATINGS**

Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{a,b}	$t \leq 10$ s	R_{thJA}	27	34	24	30	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	6	7.5	3.2	4	

Notes

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 69 °C/W for channel-1 and 64 °C/W for channel-2.

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

Parameter	Symbol	TEST CONDITIONS		Min.	Typ.	Max.	Unit
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30	-	-	V
			Ch-2	30	-	-	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	Ch-1	-	18.4	-	mV/°C
			Ch-2	-	30	-	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	Ch-1	-	-4.3	-	mV/°C
			Ch-2	-	-5	-	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1	-	2.4	V
			Ch-2	1	-	2.4	
Gate Source Leakage	I _{GSS}	V _{DS} =0 V, V _{GS} = +20 V, -16 V	Ch-1	-	-	± 100	nA
			Ch-2	-	-	± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1	-	-	1	μA
			Ch-2	-	-	1	
		V _{DS} = 30 V, V _{GS} =0 V, T _J = 55 °C	Ch-1	-	-	5	
			Ch-2	-	-	5	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V,V _{GS} = 10 V	Ch-1	10	-	-	A
			Ch-2	10	-	-	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15.6 A	Ch-1	-	0.0079	0.0095	Ω
		V _{GS} = 10 V, I _D = 20 A	Ch-2	-	0.0042	0.0051	
		V _{GS} = 4.5 V, I _D = 13 A	Ch-1	-	0.0110	0.0137	
		V _{GS} = 4.5 V, I _D = 20 A	Ch-2	-	0.0058	0.0070	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15.6 A	Ch-1	-	37	-	S
		V _{DS} = 15 V, I _D = 20 A	Ch-2	-	60	-	
Dynamic ^a							
Input Capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	-	760	-	pF
Output Capacitance	C _{oss}		Ch-2	-	1552	-	
		Reverse Transfer Capacitance	C _{rss}	Channel-2 V _{DS} =15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	-	
Ch-2	-				450	-	
C _{rss} / C _{iss} Ratio			Ch-1	0.042	-	0.084	-
			Ch-2	0.025	-	0.050	
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 15.6 A	Ch-1	-	12.3	19	nC
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	Ch-2	-	22.6	35	
			Ch-1	-	5.6	9	
			Ch-2	-	10.1	16	
Gate-Source Charge	Q _{gs}	Channel-1 V _{DS} = 15 V,V _{GS} = 4.5 V, I _D = 15.6 A	Ch-1	-	2.3	-	
Gate-Drain Charge	Q _{gd}		Ch-2	-	4.2	-	
		Output Charge	Q _{oss}	Channel-2 V _{DS} = 15 V,V _{GS} = 4.5 V, I _D = 20 A	Ch-1	-	
Ch-2	-				1.8	-	
Gate Resistance	R _g	f = 1 MHz	Ch-1	-	6.6	-	Ω
			Ch-2	-	12.4	-	
Gate Resistance	R _g	f = 1 MHz	Ch-1	0.3	1.7	3.4	Ω
			Ch-2	0.3	1.3	2.6	



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	TEST CONDITIONS	Min.	Typ.	Max.	Unit	
Dynamic ^a							
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≡ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	13	20	ns
			Ch-2	-	22	33	
Rise Time	t _r		Ch-1	-	55	85	
			Ch-2	-	82	123	
Turn-Off Delay Time	t _{d(off)}	Chan nel-2 V _{DD} =15 V, R _L = 1.5 Ω I _D ≡ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	16	25	
			Ch-2	-	20	30	
Fall Time	t _f		Ch-1	-	7	14	
			Ch-2	-	7	14	
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≡ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	8	16	
			Ch-2	-	10	20	
Rise Time	t _r		Ch-1	-	11	20	
			Ch-2	-	12	20	
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} =15 V, R _L = 1.5 Ω I _D ≡ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	12	20	
			Ch-2	-	16	30	
Fall Time	t _f		Ch-1	-	7	15	
			Ch-2	-	7	12	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	Ch-1	-	-	13.9	A
			Ch-2	-	-	25.8	
Pulse Diode Forward Current (t = 100 μs)	I _{SM}		Ch-1	-	-	100	
			Ch-2	-	-	150	
Body Diode Voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V	Ch-1	-	0.8	1.2	V
			Ch-2	-	0.82	1.2	
Body Diode Reverse Recovery Time	t _{rr}	Channel-1 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	20	35	ns
			Ch-2	-	26	40	
Body Diode Reverse Recovery Charge	Q _{rr}		Ch-1	-	9	20	nC
			Ch-2	-	20	30	
Reverse Recovery Fall Time	t _a	Channel-2 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	11.5	-	ns
			Ch-2	-	18.1	-	
Reverse Recovery Rise Time	t _b		Ch-1	-	8.5	-	
			Ch-2	-	7.9	-	

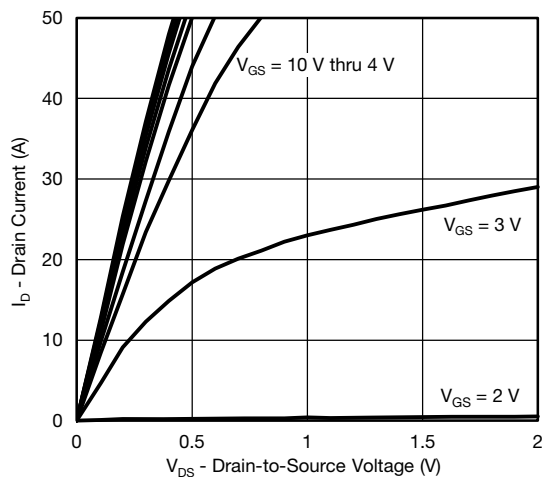
Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

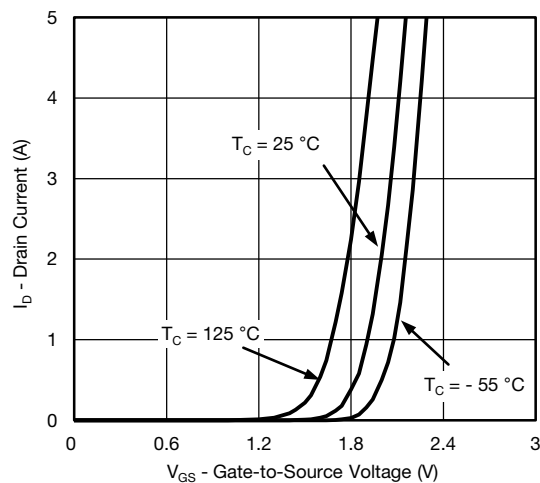
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



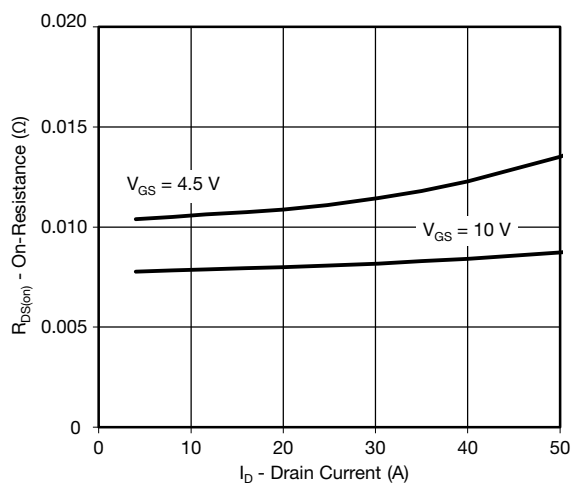
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



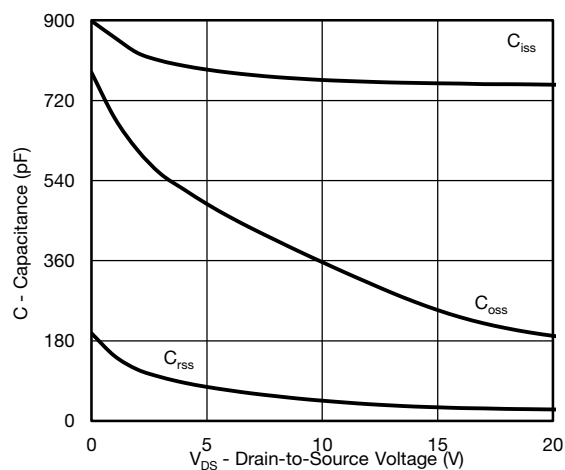
Output Characteristics



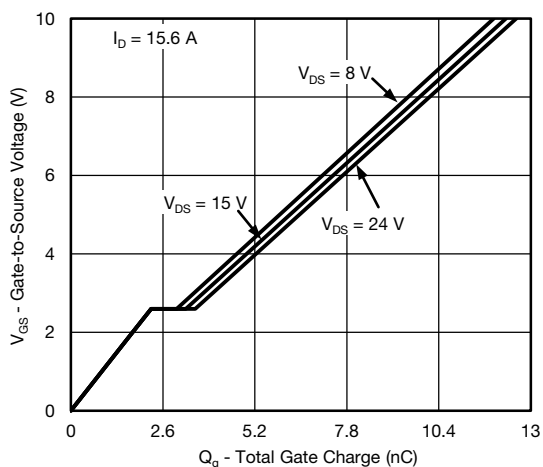
Transfer Characteristics



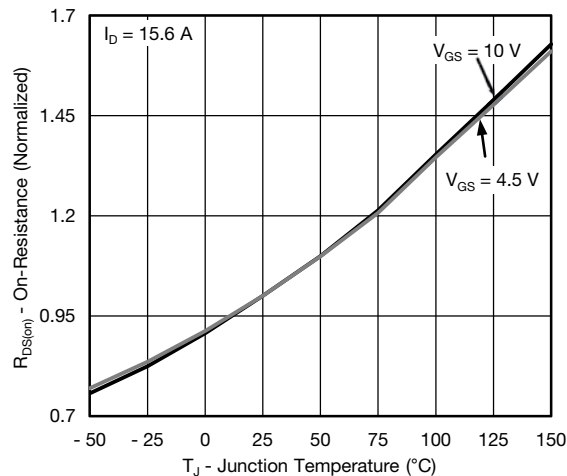
On-Resistance vs. Drain Current



Capacitance



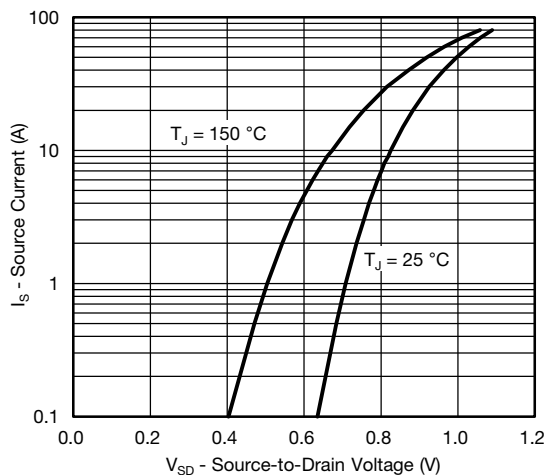
Gate Charge



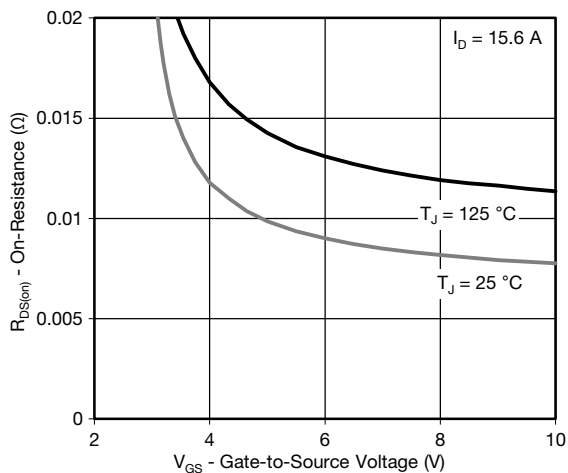
On-Resistance vs. Junction Temperature



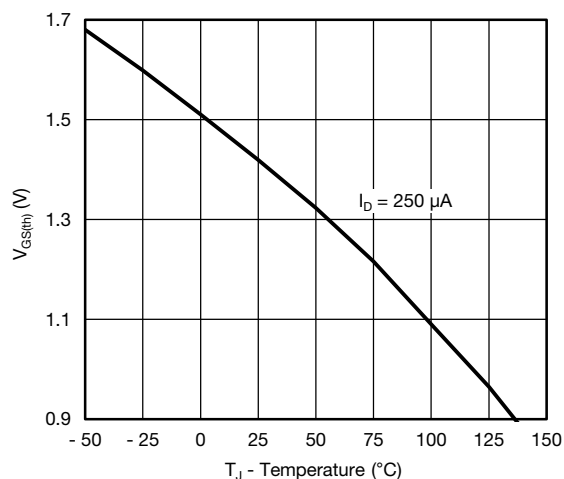
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



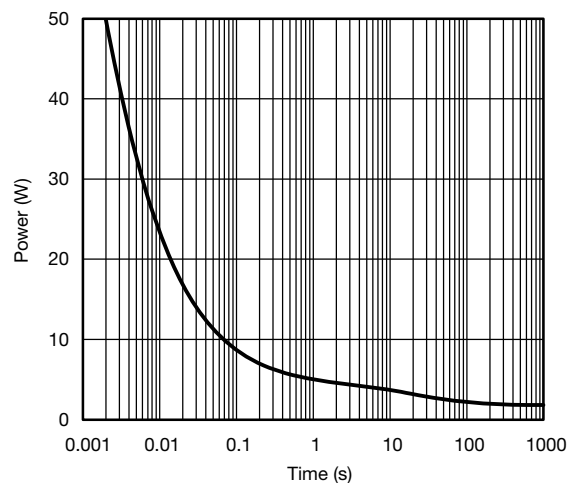
Source-Drain Diode Forward Voltage



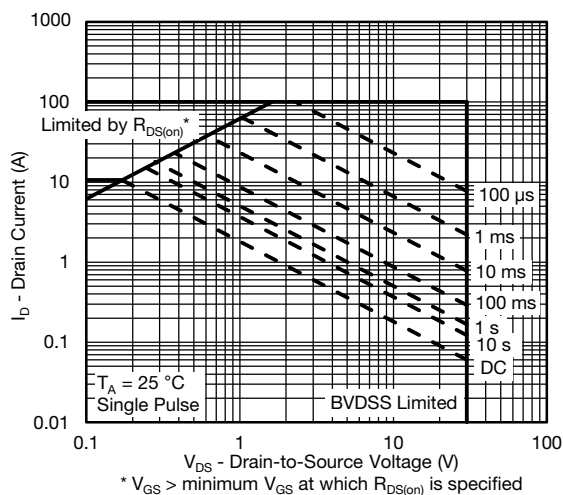
On-Resistance vs. Gate-to-Source Voltage



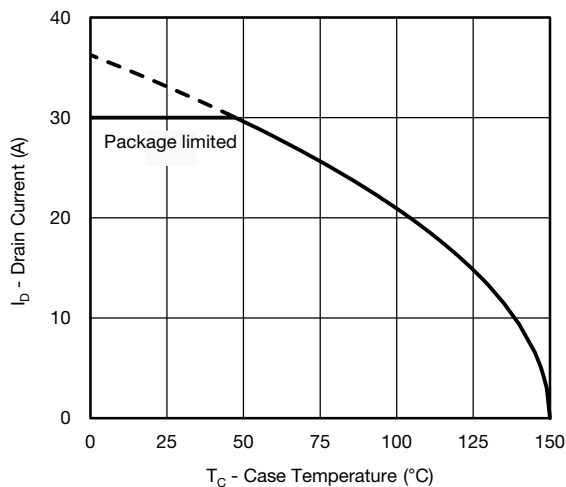
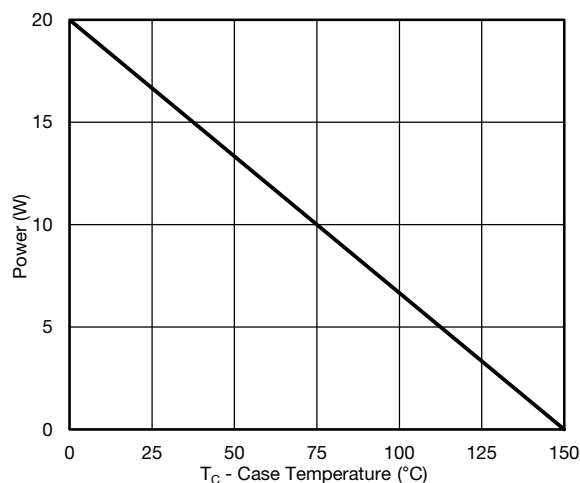
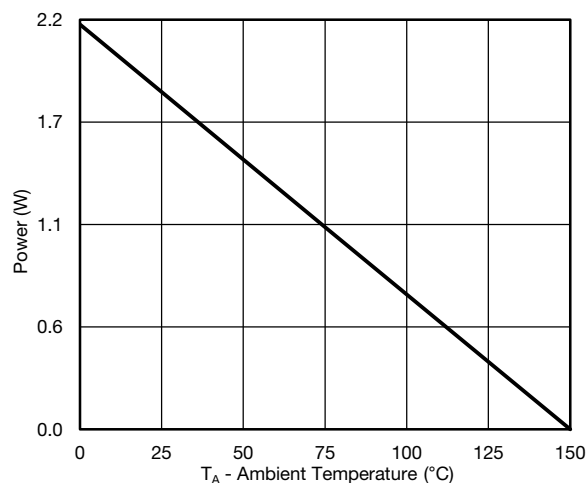
Threshold Voltage



Single Pulse Power



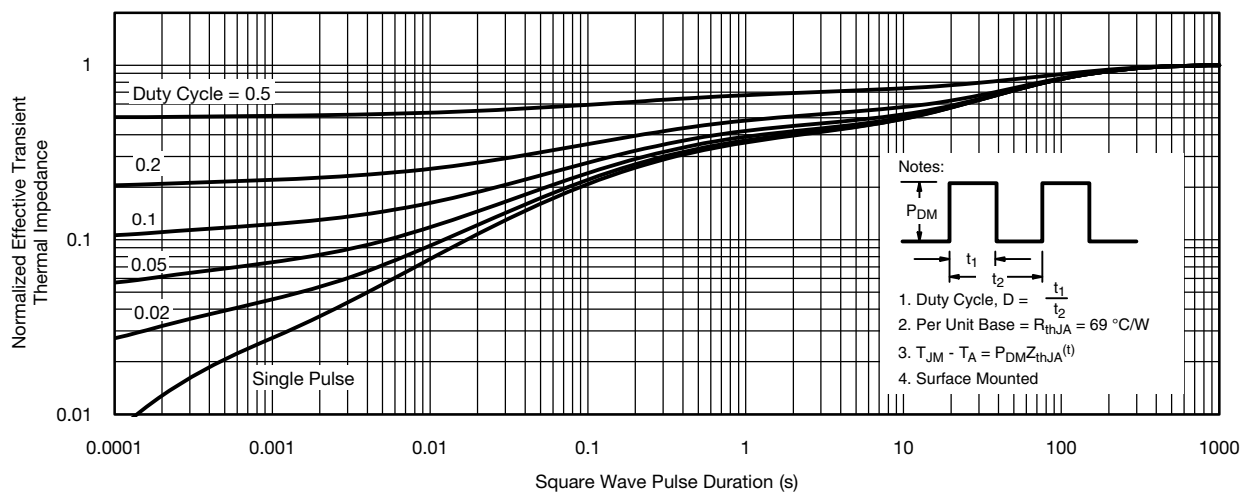
Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Case

Power, Junction-to-Ambient

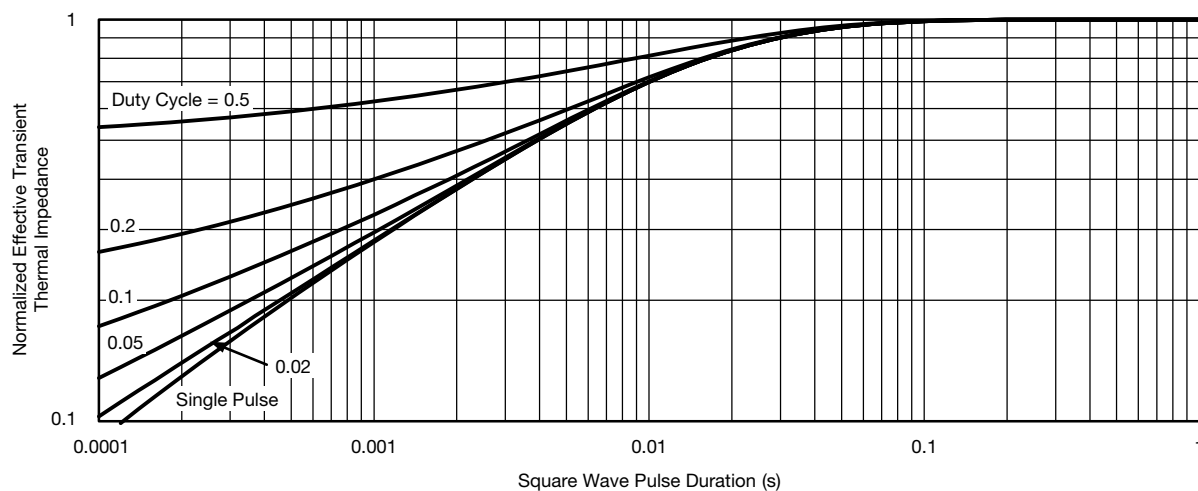
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



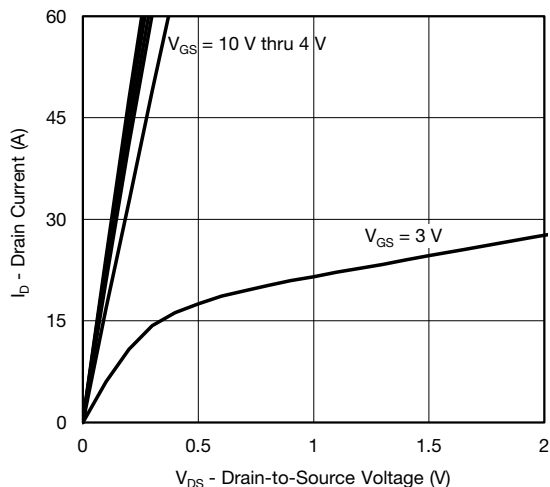
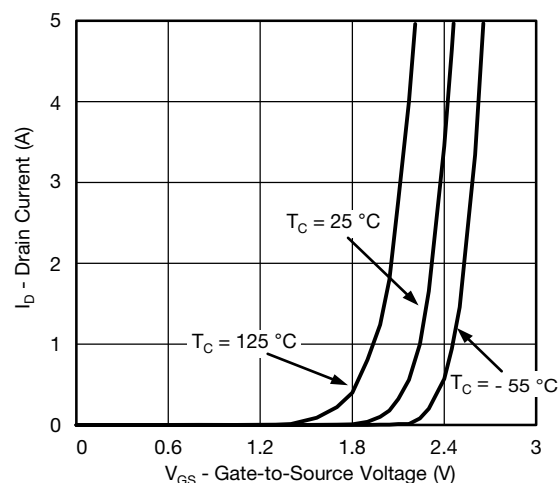
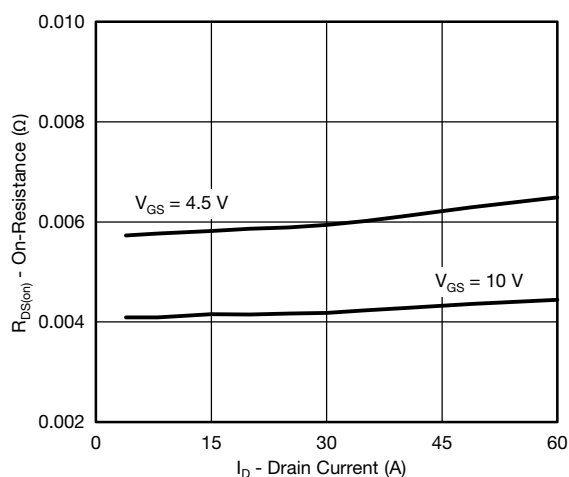
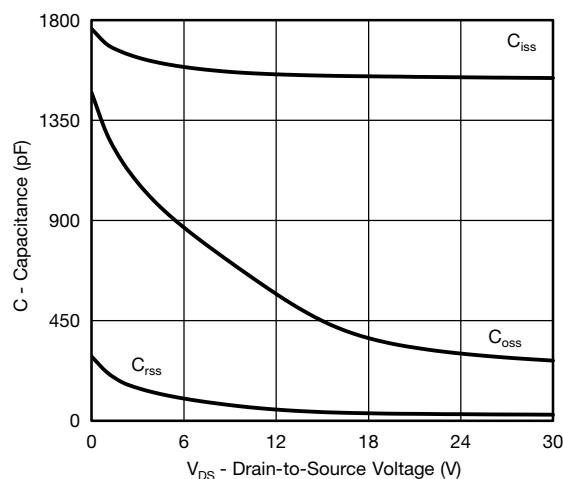
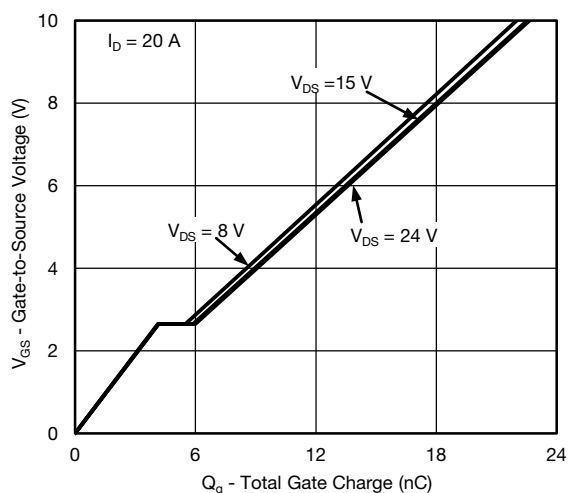
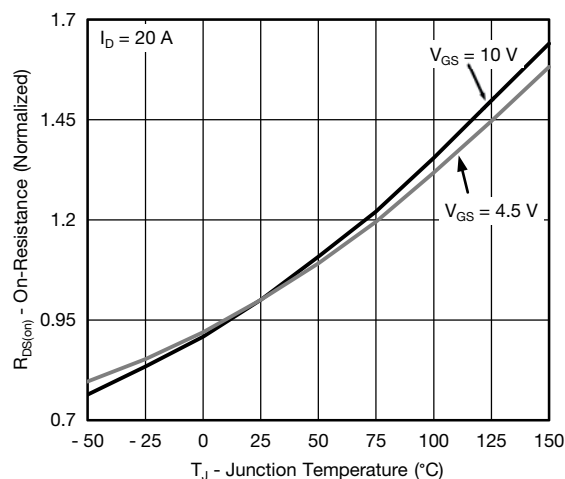
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

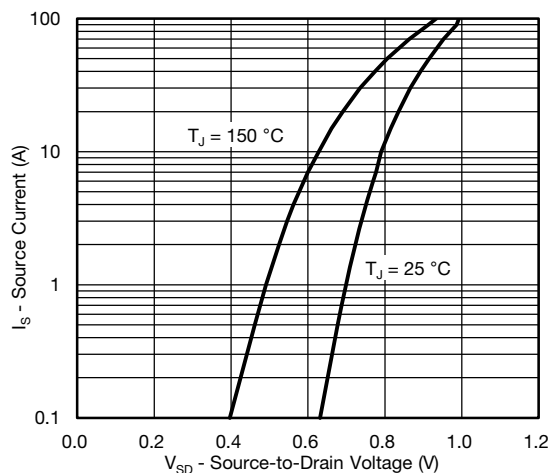


Normalized Thermal Transient Impedance, Junction-to-Case

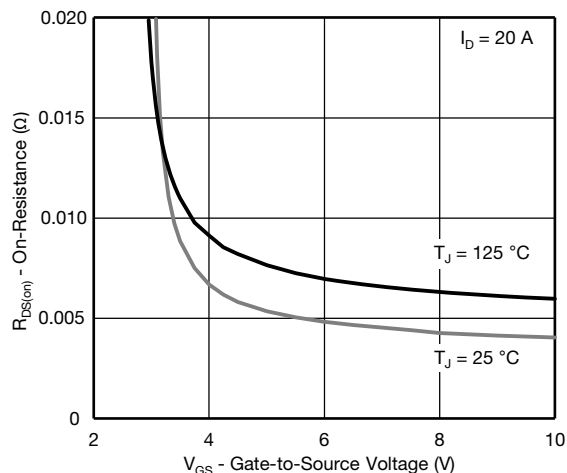
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



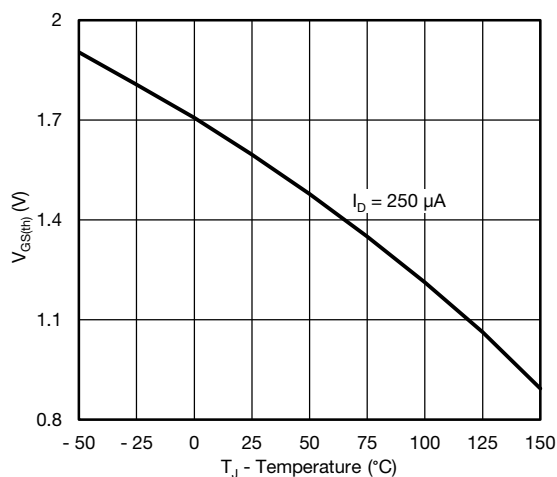
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



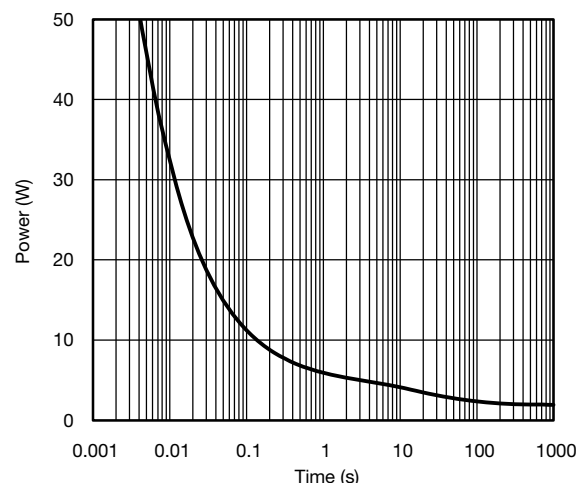
Source-Drain Diode Forward Voltage



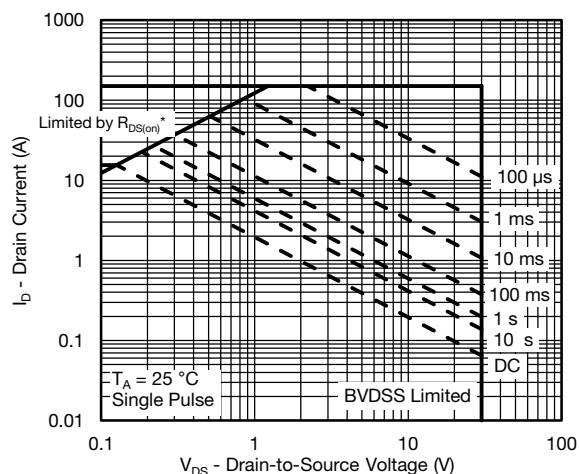
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



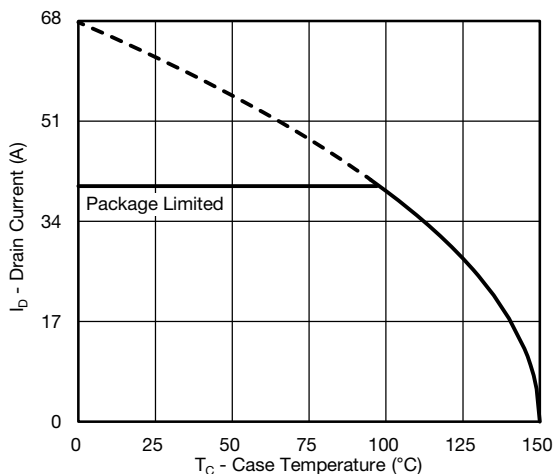
Single Pulse Power



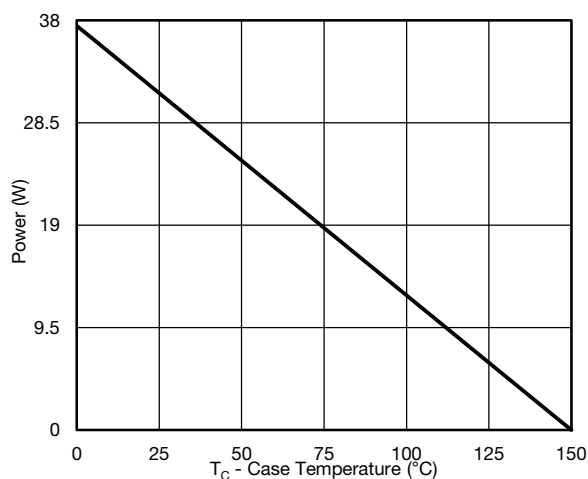
Safe Operating Area, Junction-to-Ambient



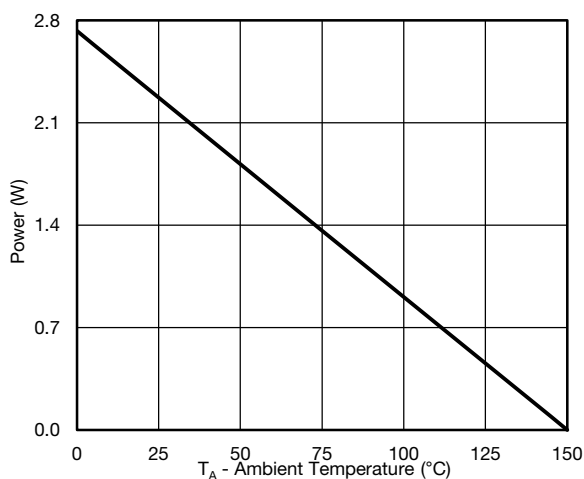
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



Power, Junction-to-Case

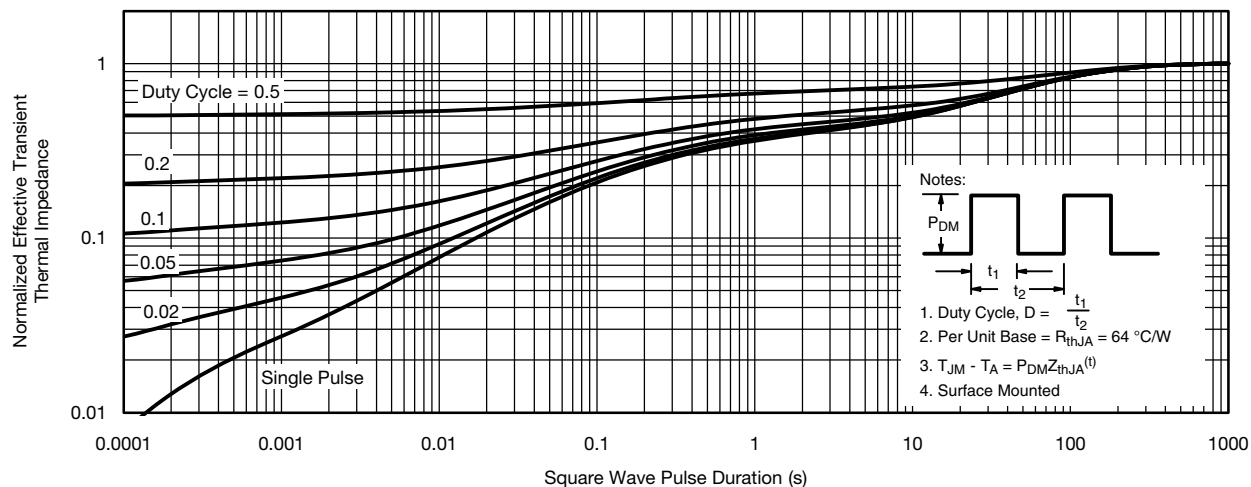


Power, Junction-to-Ambient

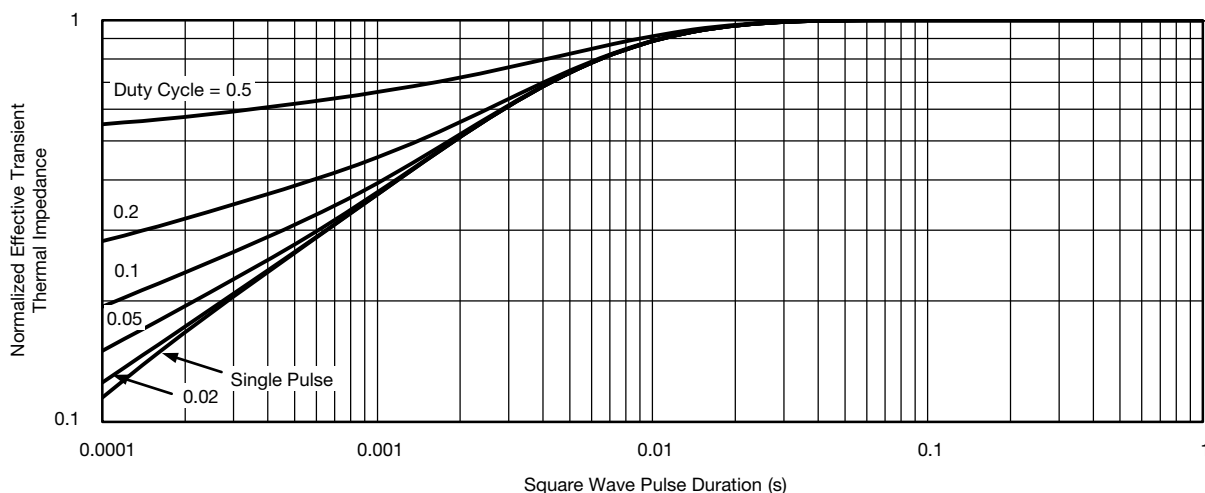
* The power dissipation P_D is based on $T_{J(max.)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

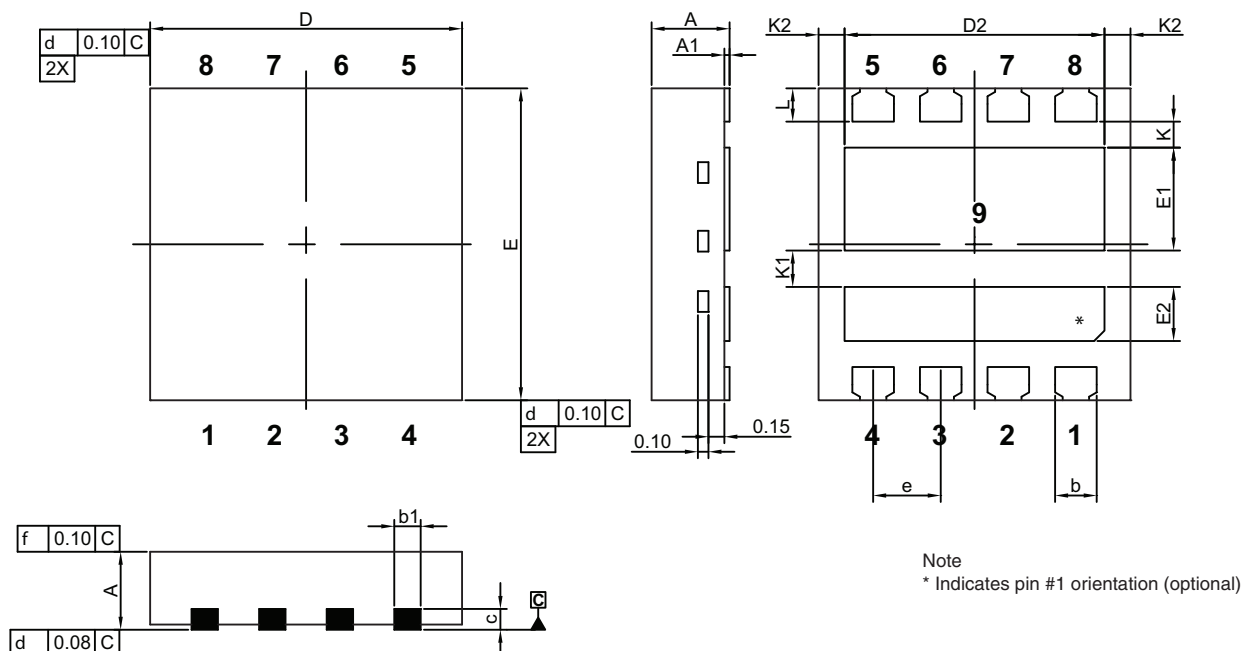


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62877.

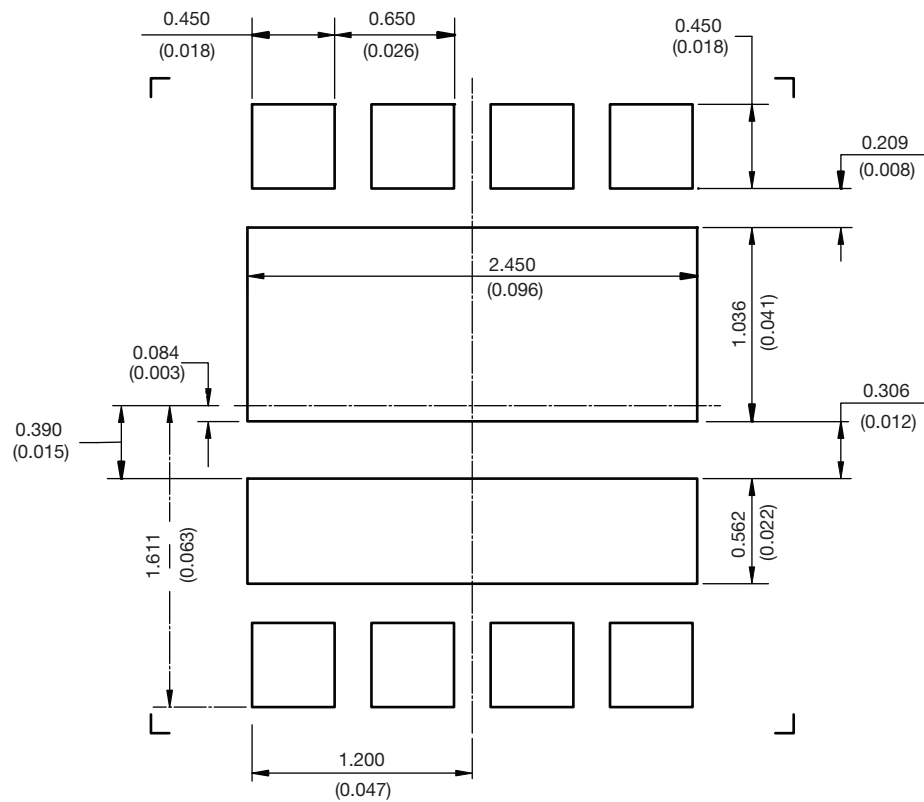


PowerPAIR® 3 x 3 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00		0.05	0.000		0.002
b	0.35	0.40	0.45	0.014	0.016	0.018
b1	0.20	0.25	0.38	0.008	0.010	0.015
C	0.18	0.20	0.23	0.007	0.008	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
D2	2.35	2.40	2.45	0.093	0.094	0.096
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	0.94	0.99	1.04	0.037	0.039	0.041
E2	0.47	0.52	0.57	0.019	0.020	0.022
e	0.65 BSC			0.026 BSC		
K	0.25 typ.			0.010 typ.		
K1	0.35 typ.			0.014 typ.		
K2	0.30 typ.			0.012 typ.		
L	0.27	0.32	0.37	0.011	0.013	0.015
ECN: T12-0347-Rev. C, 18-Jun-12						
DWG: 5998						

RECOMMENDED MINIMUM PAD FOR PowerPAIR® 3 x 3



Recommended PAD for PowerPAIR 3 x 3

Dimensions in millimeters (inches)

Keep-Out 3.5 mm x 3.5 mm for non terminating traces



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9